

isc N-Channel Mosfet Transistor

IRF614

• FEATURES

- Low $R_{DS(on)}$
- V_{GS} Rated at $\pm 20V$
- Silicon Gate for Fast Switching Speed
- Rugged
- Low Drive Requirements

• DESCRIPTION

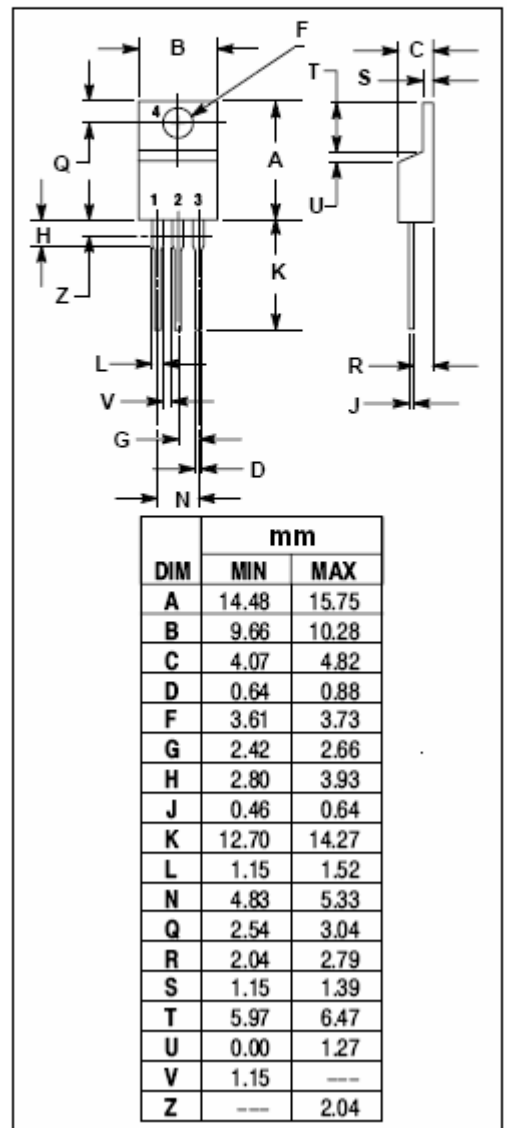
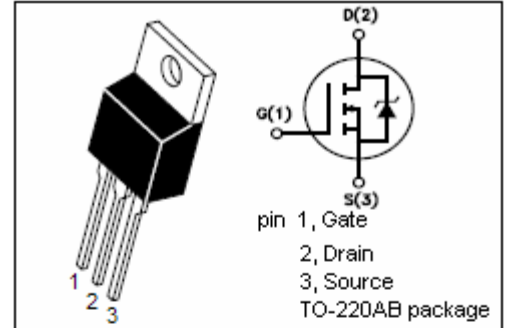
- Designed for high speed applications, such as switching power supplies , AC and DC motor controls, relay and solenoid drivers and other pulse.

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	250	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	2	A
I_{DM}	Drain Current-Single Plused	8	A
P_D	Total Dissipation @ $T_C=25^{\circ}C$	20	W
T_j	Max. Operating Junction Temperature	-55~150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	6.4	$^{\circ}C/W$
$R_{th j-a}$	Thermal Resistance,Junction to Ambient	62.5	$^{\circ}C/W$



isc N-Channel Mosfet Transistor**IRF614****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=0.25\text{mA}$	250		V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.25\text{mA}$	2	4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=1.5\text{A}$		2	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$		± 500	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=250\text{V}; V_{GS}=0$		250	μA
V_{SD}	Forward On-Voltage	$I_S=2\text{A}; V_{GS}=0$		2.0	V